

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
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PTO/SB/05A(10-01)  
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Complete if Known

Application Number 08/902,133

Filing Date July 29, 1997

First Named Inventor Forbes, Leonard

Group Art Unit 2815

Examiner Name

Bekert H, George A. Wilson

Attorney Docket No: 303.356US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
<i>OW</i>	US-2005/0146934 A1	07/07/2005	Forbes, L., et al.	03/07/2005
<i>OW</i>	US-6,936,849	08/30/2005	Forbes, L., et al.	07/29/1997

CLASS  
Sub**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T <sup>2</sup>
<i>OW</i>	JP-06-013626	01/21/1994	Igarashi, Y.	
<i>OW</i>	JP-56056677	05/18/1981	Aoyama, Masaharu, et al.	
<i>OW</i>	JP-7326718	12/12/1995	Itakura, Toru	
<i>OW</i>	JP-7326718 -Translation	12/12/1995	Itakura, Toru	

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1**OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS**

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<i>OW</i>		FREITAS, ROBERT A., "Nanomedicine, Volume I: Basic Capabilities, Appendix A", Landes Bioscience, Georgetown, TX, <a href="http://www.nanomedicine.com/NMI/AppendixA.htm">http://www.nanomedicine.com/NMI/AppendixA.htm</a> , (1999), 23 pages *	
<i>OW</i>		MICHAELSON, HERBERT B., "The work function of the elements and its periodicity", Journal of Applied Physics, 48(11), (November 1977), 4729-4733	
<i>OW</i>		PIERRET, ROBERT F., "Field Effect Devices", Modular Series on Solid State Devices, Volume IV, Addison-Wesley Publishing Company, Reading, MA, (1983), 23, 63 *	

\* No month cited in doc.

EXAMINER

*A. Wilson*

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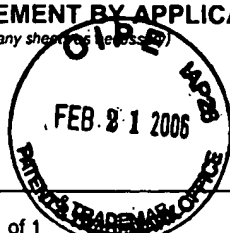
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Application Number	08/902,133
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Wilson, Allan

Sheet 1 of 1

Attorney Docket No: 303.356US1

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<i>W</i>	US-2006/0017095 A1	01/26/2006	Forbes, L., et al.	09/27/2005
<i>W</i>	US-2006/0024878 A1	02/02/2006	Forbes, L., et al.	09/27/2005
<i>W</i>	US-4,929,985	05/29/1990	Takasaki, K.	05/02/1989
<i>W</i>	US-7,005,344	02/28/2006	Forbes, L., et al.	06/18/2001

CLASS  
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1**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	
<i>W</i>	JP-62-086867	04/21/1987	Honjo, K.	
<i>W</i>	JP-63-128760	01/06/1988	Toyokazu, Onishi	

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Sheet 1 of 1

Form 1449\*

Atty. Docket No.: 303.356US1

Serial No. 08/902,133

INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: ~~2503~~ 2815

## U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>DMW</i>	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
<i>DMW</i>	5,754,477	05/19/1998	Forbes	365	185.33	01/29/97

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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## OTHER DOCUMENTS

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Sheet 1 of 7

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INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2805 2815

## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>Vmw</i>	4,507,673	03/26/1985	Aoyama, et al.	357	257	09/21/83
<i>Vmw</i>	4,893,273	01/09/1990	Usami	365	185-185.04	03/21/86
<i>Vmw</i>	5,111,430	05/05/1992	Morie	365	185-185.24	06/21/90
<i>Vmw</i>	5,260,593	11/09/1993	Lee	257	316	12/10/91
<i>Vmw</i>	5,293,560	03/08/1994	Harari	365	185-185.03	11/03/92
<i>Vmw</i>	5,369,040	11/29/1994	Halvis, et al.	427	433	04/12/93
<i>Vmw</i>	5,449,941	09/12/1995	Yamazaki, et al.	257	411	10/27/92
<i>Vmw</i>	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
<i>Vmw</i>	5,477,485	12/19/1995	Bergemont, et al.	365	185.24	02/22/95
<i>Vmw</i>	5,508,543	04/16/1996	Hartstein, et al.	257	314	04/29/94
<i>Vmw</i>	5,530,581	06/25/1996	Cogan	359	265	05/31/95
<i>Vmw</i>	5,580,380	12/03/1996	Liu, et al.	117	86	01/30/95
<i>Vmw</i>	5,670,790	09/23/1997	Katoh, et al.	257	14	09/19/96

## FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes I No
<i>Vmw</i>	3-222367	10/01/1994	Japan	H01L	29/784	
<i>Vmw</i>	6-224431	08/12/1994	Japan	H01L	29/784	
<i>Vmw</i>	6-302828	10/28/1994	Japan	H01L	29/788	
<i>Vmw</i>	8-255878	10/01/1996	Japan	H01L	27/10	

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
<i>Vmw</i>	Akasaki, I., et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N (0 < x (< or =) 0.4) Films Grown on Sapphire Substrate by MOVPE", <u>J. Crystal Growth</u> , <b>98</b> , 209-219, (1989)
<i>Vmw</i>	Alok, D., et al., "Electrical Properties of Thermal Oxide Grown on N-type 6H-Silicon Carbide", <u>Applied Physics Letters</u> , <b>64</b> , 2845-2846, (May 23, 1994)
<i>Vmw</i>	Andrieux, M., et al., "Interface and Adhesion of PACVD SiC Based Films on Metals", <u>Supp. "Le Vide: science, technique et applications"</u> , <b>279</b> , 212-214, (1996)
<i>Vmw</i>	Bachmann, P., et al., "Influence on Surface Modifications on the Electronic Properties of CVD Diamond Films", <u>Diamond and Related Materials</u> , <b>5</b> , 1378-1383, (1996)
<i>Vmw</i>	Baglee, D., "Characteristics & Reliability of 100 Angstrom Oxides", <u>IEEE 22nd Annual Proc. Reliability Physics</u> , Las Vegas, 152-155, (April 3-5, 1984)

Examiner

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Sheet 2 of 7

Form 1449\*

Atty. Docket No.: 303.356USI

Serial No. 08/502,133

INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2503 2815

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

Vmur	Beheim, G., et al., "Magnetron Plasma Etching of SiC for Microstructures", <u>Proc: SPIE - Integrated Optics and Microstructures III</u> , San Jose, CA, 82-86, (Jan 29, 1996)
Vmur	Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", <u>Japanese J. Applied Physics</u> , 35, 4175-4181, (1996)
Vmur	Benjamin, M., et al., "UV Photoemission Study of Heteroepitaxial AlGaN Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, 455-460, (1996)
Vmur	Bermudez, V., et al., "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", <u>J. Applied Physics</u> , 79, 110-119, (Jan. 1996)
Vmur	Casey, H., et al., "Low Interface Trap Density for Remote Plasma Deposited SiO <sub>2</sub> on n-type GaN", <u>Applied Phys. Lett.</u> , 68, 1850-1852, (March 1996)
Vmur	Chang, C., et al., "Novel Passivation Dielectrics-The Boron- or Phosphorus-Doped Hydrogenated Amorphous Silicon Carbide Films", <u>Journal of the Electrochemical Society</u> , 132, 418-422, (Feb. 1985)
Vmur	Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", <u>Materials Chemistry and Physics</u> , 45, 176-179, (1996)
Vmur	Clarke, G., et al., "The Infrared Properties of Magnetron-Sputtered Diamond-Like Thin Films", <u>Thin Solid Films</u> , 280, 130-135, (1996)
Vmur	Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", <u>J. Materials Res.</u> , 11, 2269-2273, (Sept. 1996)
Vmur	Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", <u>Vacuum</u> , 46, 349-355, (1995)
Vmur	Demichelis, F., et al., "Influence of Doping on the Structural and Optoelectronic Properties of Amorphous and Microcrystalline Silicon Carbide", <u>Journal of Applied Physics</u> , 72, 1327-1333, (Aug. 15, 1992)
Vmur	Demichelis, F., et al., "Physical Properties of Undoped and Doped Microcrystalline SiC:H Deposited By PECVD", <u>Materials Research Society Symposium Proceedings</u> , 219, Anaheim, CA, 413-418, (4/30 - 5/3, 1991)
Vmur	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, 48-52, (1993)

Examiner V. Martin WilsonDate Considered 3/3/99

\*Substitute Disclosure Statement Form (PTO-1449)

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Sheet 3 of 7

Form 1449\*

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Serial No. 08/002,133

INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2585-2815

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

- Vmms* Fissel, A., et al., "Epitaxial Growth of SiC Thin Films on Si-stabilized alpha-SiC (0001) at Low Temperatures by Solid-source Molecular Beam Epitaxy", Journal of Crystal Growth, 154, 72-80, (1995)
- Vmms* Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", J. Applied Physics, 79, 7814-7819, (May 15, 1996)
- Vmms* Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", Journal of Non-Crystalline Solids, 198-200, 577-581, (1996)
- Vmms* Goetzberger, A., et al., Applied Solid State Science: Advances in Materials and Device Research, R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)
- Vmms* Gaul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", Applied Phys. Lett., 21, 67-69, (July 1972)
- Vmms* Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", Materials Research Society Symposium Proceedings, 164, Boston, MA, 291-301, (11/29-12/1, 1989)
- Vmms* He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", Thin Solid Films, 260, 32-37, (1995)
- Vmms* Hu, G., "Will Flash Memory Replace Hard Disk Drive?", IEEE Electron Devices Meeting, Session 24, (Dec. 13, 1994)
- Vmms* Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", Thin Solid Films, 272, 4-6, (1996)
- Vmms* Jou, S., et al., "Electron Emission Characterization of Diamond Thin Films Grown from a Solid Carbon Source", Thin Solid Films, 280, 256-261, (1996)
- Vmms* Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", J. Electronic Materials, 25, 875-878, (1996)
- Vmms* Kumbhar, A., et al., "Growth of Clean Amorphous Silicon-Carbon Alloy Films by Hot-Filament Assisted Chemical Vapor Deposition Technique", Applied Phys. Lett., 66, 1741-1743, (April 1995)
- Vmms* Lakshmi, E., et al., "Interface-State Characteristics of GaN/GaAs MIS Capacitors", Solid-State Electronics, 25, 811-815, (1982)

Examiner

Date Considered

3/3/99

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Atty. Docket No.: 303.356USI

Serial No. 08/902,133

Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2503-2815

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

- Vmws Lanois, F., et al., "Angle Etch Control for Silicon Carbide Power Devices", Applied Phys. Lett., 69, 236-238, (July 1996)
- Vmws Lau, S., et al., "Optoelectronic Properties of Highly Conductive Microcrystalline SiC Produced by Laser Crystallization of Amorphous SiC", J. of Non-Crystalline Solids, 198-200, 907-910, (1996)
- Vmws Leggieri, G., et al., "Laser Ablation Deposition of Silicon Carbide Films", Applied Surface Science, 96-98, 866-869, (1996)
- Vmws Lei, T., et al., "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", J. Appl. Phys., 71, 4933-4943, (May 1992)
- Vmws Liu, J., et al., "Formation of SiC Films on Silicon Field Emitters", Materials Res. Soc. Symp. Proc., 311, San Francisco, CA, (April 13-15, 1993)
- Vmws Liu, J., et al., "Modification of Si Field Emitter Surfaces by Chemical Conversion to SiC", J. Vac. Sci. Technology, B 12, 717-721, (1994)
- Vmws Luo, J., et al., "Localized Epitaxial Growth of Hexagonal and Cubic SiC Films on Si by Vacuum Annealing", Applied Phys. Lett., 69, 916-918, (Aug. 1996)
- Vmws Martins, R., et al., "Transport Properties of Doped Silicon Oxycarbide Microcrystalline Films Produced by Spatial Separation Techniques", Solar Energy Materials and Solar Cells, 41-42, 493-517, (1996)
- Vmws Martins, R., et al., "Wide Band Gap Microcrystalline Silicon Thin Films", Diffusion and Defect Data: Solid State Phenomena, 44-46, Part 1, Scitec Publications, 299-346, (1995)
- Vmws Maury, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", Surface and Coatings Technology, 76-77, 119-125, (1995)
- Vmws McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", Applied Phys. Lett., 68, 3755-3757, (June 1996)
- Vmws Mogab, C., et al., "Conversion of Si to Epitaxial SiC by Reaction with C(2)H(2)", J. Applied Physics, 45, 1075-1084, (March 1974)
- Vmws Molnar, R., et al., "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", J. Appl. Phys., 76, 4587-4595, (1994)

Examiner

V. Markie Wallace

Date Considered

3/3/99

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Form 1449\*

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INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2505-2815

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

- vmw Muller, K., et al., "Trench Storage Node Technology for Gigabit DRAM Generations", Digest IEEE Int. Electron Devices Meeting, San Francisco, CA, 594-597, (Dec. 1996)
- vmw Nemanich, P., et al., "Diamond Negative Electron Affinity Surfaces, Structures and Devices", Proc. : Third International Conference on Applications of Diamond Films and Related Materials, 1, Gaithersburg, MD, 17-24, (1995)
- vmw Nemanich, R., et al., "Negative Electron Affinity Surfaces of Aluminum Nitride and Diamond", Diamond and Related Materials, 5, 790-796, (1996)
- vmw Ouyang, M., et al., "Deposition of Diamond-Like Carbon Films via Excimer Laser Ablation of Polybutadiene", Materials Science and Engineering, B39, 228-231, (1996)
- vmw Pankove, J., "Photoelectric Emission", In: Optical Processes in Semiconductors, Dover Publications Inc., New York, 287-301, (1971)
- vmw Pankove, J., et al., "Photoemission from GaN", Applied Phys. Lett., 25, 53-55, (1974)
- vmw Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", IEEE Transaction on Electron Devices, 42, 678-682, (April 1995)
- vmw Patuwathavithane, C., et al., "Oxidation Studies for 6H-SiC", Proc. 4th Int. Conf. on Amorphous and Crystalline Silicon Carbide IV, Santa Clara, CA, 163-169, (Oct. 9-11, 1991)
- vmw Pereyra, I., et al., "Wide Gap a-Si(1-x)C(x): H Thin Films Obtained Under Starving Plasma Deposition Conditions", J. Non-Crystalline Solids, 201, 110-118, (1996)
- vmw Pollack, S., "Electron Transport Through Insulating Thin Films", Appl. Solid-State Science, 1, 345-355, (1969)
- vmw Prendergast, J., "FLASH or DRAM: Memory Choice for the Future", IEEE Electron Device Meeting. Session 25, Phoenix, AZ, (1995)
- vmw Rahman, M., et al., "Preparation and Electrical Properties of An Amorphous SiC/ Crystalline Si p(+)/n Heterostructure", Japanese J. Applied Physics, 23, 515-524, (May 1984)

Examiner

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Sheet 6 of 7

Form 1449\*

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Serial No. 08/902,433

INFORMATION DISCLOSURE STATEMENT  
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Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2503 2815

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

- Renlund, G., et al., "Silicon Oxycarbide Glasses: Part I. Preparation and Chemistry", Journal of Materials Research, 6, 2716-2722, (December 1991)
- Renlund, G., et al., "Silicon Oxycarbide Glasses: Part II. Structure and Properties", Journal of Materials Research, 6, 2723-2734, (December 1991)
- Schmidt, T., et al., "Low Temperature Diamond Growth Using Fluorinated Hydrocarbons", Diamond and Related Materials, 5, 1318-1322, (1996)
- Serre, C., et al., "Ion-Beam Synthesis of Amorphous SiC Films: Structural Analysis and Recrystallization", J. Appl. Phys., 79, 6907-6913, (May 1996)
- Sim, S., et al., "A New Planar Stacked Technology (PST) for Scaled and Embedded DRAMs", Digest IEEE Int. Electron Devices Meeting, San Francisco, CA, 504-507, (Dec. 1996)
- Suzaki, Y., et al., "Quantum Size Effects of a-Si(:H)/a-SiC(:H) Multilayer Films Prepared by rf Sputtering", Abstracts of Papers Published in the Int. J. Japanese Soc. for Precision Engineering, 28, Abstract of Paper in vol. 60, 182, (June 1994)
- Svirkova, N., et al., "Deposition Conditions and Density-of-States Spectrum of a-Si(1-x)C(x) :H Films Obtained by Sputtering", Semiconductors, 28, 1164-1169, (Dec. 1994)
- Sze, S., Physics of Semiconductors, 2nd Edition., John Wiley & Sons, Pub., New York, ISBN 0471056618, (1981)
- Tarui, Y., "Flash Memory Features Simple Structure, Superior Integration", JEE, 30, 84-87, (Sept. 1993)
- Tenhover, M., et al., "DC-Magnetron Sputtered Silicon Carbide", Materials Res. Soc. Symp. Proc., 356, Boston, MA, 227-232, (11/28-12/02, 1994)
- Thomas, J., et al., "Plasma Etching and Surface Analysis of a-SiC :H Films Deposited by Low Temperature Plasma Enhanced Chemical Vapor Deposition", Materials Res. Soc. Symp. Proc., 334, Boston, MA, 445-450, (11/29-12/02, 1993)
- Tiwari, S., et al., "A silicon nanocrystal based memory", Appl. Physics Lett., 68, 1377-1379, (1996)
- Tiwari, S., et al., "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage", Abstract of IEEE Int. Electron Devices Meeting, Washington, DC, 521-524, (Dec. 1995)

Examiner

V. Martin Wallace

Date Considered

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Sheet 7 of 7

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(Including Author, Title, Date, Pertinent Pages, Etc.)

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InitialTucker, C., et al., "Ion-beam-assisted Deposition of Nonhydrogenated a-Si:C Films", Can. J. Physics, 74, 97-101, (1996)van der Weide, J., et al., "Negative-electron-affinity Effects on the Diamond (100) Surface", Physical Review B (Condensed Matter), 50, 5803-5806, (Aug. 15, 1994)Vodakov, Y., et al., "Diffusion and Solubility of Impurities in Silicon Carbide", In: Silicon Carbide, R.C. Marshall, et al., eds., Univ. of South Carolina Press, 508-519, (1973)Wahab, Q., et al., "3C-SiC / Si / 3C-SiC Epitaxial Trilayer Films Deposited on Si (111) Substrates by Reactive Magnetron Sputtering", J. Materials Res., 10, 1349-1351, (June 1995)Watanabe, A., et al., "SiC Thin Film Preparation by ArF Excimer Laser Chemical Vapor Deposition. Part 1: Rate of Photolysis of Alkylsilanes by ArF Excimer Laser and their Decomposition Products", Thin Solid Films, 274, 70-75, (1996)Wolter, S., et al., "Textured Growth of Diamond on Silicon via in situ Carburization and Bias-Enhanced Nucleation", Appl. Phys. Lett., 62, 1215-1217, (March 1993)Wu, K., et al., "The Growth and Characterization of Silicon/Silicon Carbide Heteroepitaxial Films on Silicon Substrates by Rapid Thermal Chemical Vapor Deposition", Japanese J. Appl. Phys., 35, 3836-3840, (1996)Yamaguchi, Y., et al., "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", Digest of Tech. Papers: 8th Int. Conf. on Solid-State Sensors and Actuators and Eurosensors IX, vol. 2, Stockholm, Sweden, 190-193, (June 1995)Yamanashi, H., et al., "Deposition of Silicon Compound Thin Films in DC Discharge Plasma Using Hydrogen-Hexamethyldisilane Gas Mixture", Proc.: Int. Symp. on Surfaces and Thin Films of Electronic Materials. Bull. of the Res. Institute of Electronics, Shizuoka University, 30, 95-98, (1995)Yee, A., et al., "The Effect of Nitrogen on Pulsed Laser Deposition of Amorphous Silicon Carbide Films: Properties and Structure", J. Materials Research, 11, 1979-1986, (1996)Yoder, M., "Wide Bandgap Semiconductor Materials and Devices", IEEE Transactions on Electron Devices, 43, 1633-1636, (October 1996)

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Date Considered

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\*Substitute Disclosure Statement Form (PTO-1449)

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